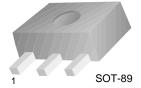


### **KSA1201**

### **Power Amplifier**

- Collector-Emitter Voltage: V<sub>CEO</sub>= -120V
- f<sub>T</sub>=120MHz
- Collector Power Dissipation P<sub>C</sub>=1~2W : Mounted on Ceramic Board
- Complement to KSC2881



1. Base 2. Collector 3. Emitter

### **PNP Epitaxial Silicon Transistor**

### **Absolute Maximum Ratings** T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-800	mA
I <sub>B</sub>	Base Current	-160	mA
P <sub>C</sub> P <sub>C</sub> *	Collector Power Dissipation	500 1,000	mW mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

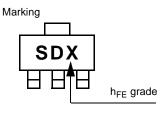
<sup>\*</sup> Mounted on Ceramic Board (250mm2 x 0.8mm)

### **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-120			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E$ = -1mA, $I_C$ =0	-5			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -120V, I <sub>E</sub> =0			-100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE}$ = -5V, $I_{C}$ =0			-100	nA
h <sub>FE</sub>	DC Current Gain	$V_{CE}$ = -5V, $I_{C}$ = -100mA	80		240	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C$ = -500mA, $I_B$ =-50mA			-1.0	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	$V_{CE}$ = -5V, $I_{C}$ = -500mA			-1.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}$ = -5V, $I_{C}$ = -100mA		120		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz			30	pF

## **h**<sub>FE</sub> Classification

Classification	0	Y	
h <sub>FE</sub>	80 ~ 160	120 ~ 240	



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# **Typical Characteristics**

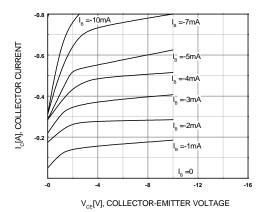


Figure 1. Static Characteristic

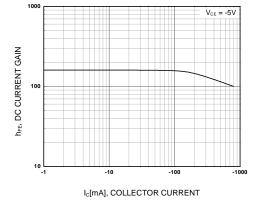


Figure 2. DC current Gain

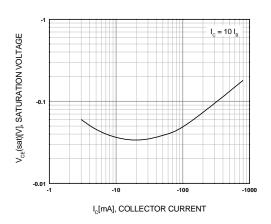


Figure 3. Collector-Emitter Saturation Voltage

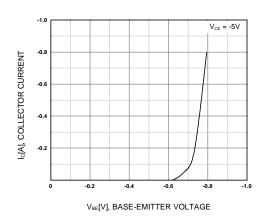


Figure 4. Base-Emitter On Voltage

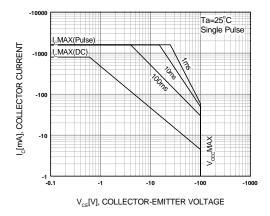


Figure 5. Safe Operating Area

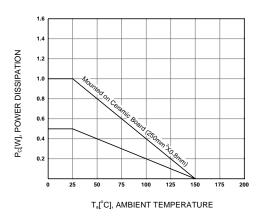
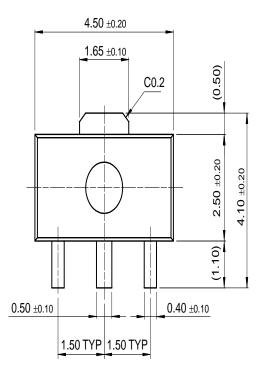


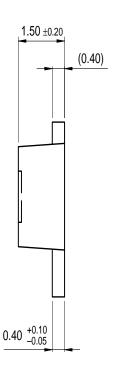
Figure 6. Power Derating

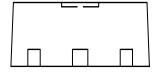
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## **Package Dimensions**

## **SOT-89**







Dimensions in Millimeters

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CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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